

SKM150GB12T4



SEMITRANS®2

Fast IGBT4 Modules

SKM150GB12T4

Features

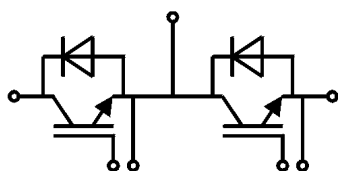
- IGBT4 = 4. Generation (Trench)IGBT
- VCEsat with positive temperature coefficient
- High short circuit capability, self limiting to $6 \times I_{CNOM}$
- Soft switching 4. Generation CAL diode (CAL4)

Typical Applications

- AC inverter drives
- UPS
- Electronic welders at fsw up to 20 kHz

Remarks

- Case temperature limited to $T_c = 125^\circ\text{C}$ max, recomm.
Top = $-40 \dots +150^\circ\text{C}$, product rel. results valid for $T_j = 150^\circ$



GB

Absolute Maximum Ratings

Symbol	Conditions		Values	Unit
IGBT				
V _{CES}			1200	V
I _C	T _j = 175 °C	T _c = 25 °C	232	A
		T _c = 80 °C	179	A
I _{Cnom}			150	A
I _{CRM}	I _{CRM} = 3xI _{Cnom}		450	A
V _{GES}			-20 ... 20	V
t _{psc}	V _{CC} = 800 V V _{GE} ≤ 15 V V _{CES} ≤ 1200 V	T _j = 150 °C	10	μs
T _j			-40 ... 175	°C
Inverse diode				
I _F	T _j = 175 °C	T _c = 25 °C	189	A
		T _c = 80 °C	141	A
I _{Fnom}			150	A
I _{FRM}	I _{FRM} = 3xI _{Fnom}		450	A
I _{FSM}	t _p = 10 ms, sin 180°, T _j = 25 °C		900	A
T _j			-40 ... 175	°C
Module				
I _{t(RMS)}			200	A
T _{stg}			-40 ... 125	°C
V _{isol}	AC sinus 50Hz, t = 1 min		4000	V

Characteristics

Symbol	Conditions	min.	typ.	max.	Unit
IGBT					
$V_{CE(sat)}$	$I_C = 150\text{ A}$ $V_{GE} = 15\text{ V}$ chipelevel	$T_j = 25^\circ\text{C}$	1.8	2.05	V
		$T_j = 150^\circ\text{C}$	2.2	2.4	V
V_{CE0}		$T_j = 25^\circ\text{C}$	0.8	0.9	V
		$T_j = 150^\circ\text{C}$	0.7	0.8	V
r_{CE}	$V_{GE} = 15\text{ V}$	$T_j = 25^\circ\text{C}$	6.7	7.7	$\text{m}\Omega$
		$T_j = 150^\circ\text{C}$	10.0	10.7	$\text{m}\Omega$
$V_{GE(th)}$	$V_{GE} = V_{CE}$, $I_C = 6\text{ mA}$	5	5.8	6.5	V
I_{CES}	$V_{GE} = 0\text{ V}$ $V_{CE} = 1200\text{ V}$	$T_j = 25^\circ\text{C}$	0.1	0.3	mA
		$T_j = 150^\circ\text{C}$			mA
C_{ies}	$V_{CE} = 25\text{ V}$ $V_{GE} = 0\text{ V}$	$f = 1\text{ MHz}$	9.3		nF
C_{oes}		$f = 1\text{ MHz}$	0.58		nF
C_{res}		$f = 1\text{ MHz}$	0.51		nF
Q_G	$V_{GE} = -8\text{ V} \dots +15\text{ V}$		850		nC
R_{Gint}	$T_j = 25^\circ\text{C}$		5.0		Ω
$t_{d(on)}$	$V_{CC} = 600\text{ V}$	$T_j = 150^\circ\text{C}$	180		ns
t_r	$I_C = 150\text{ A}$ $V_{GE} = \pm 15\text{ V}$	$T_j = 150^\circ\text{C}$	42		ns
		$T_j = 150^\circ\text{C}$	19.2		mJ
E_{on}	$R_{G on} = 1\text{ }\Omega$	$T_j = 150^\circ\text{C}$	410		ns
$t_{d(off)}$	$R_{G off} = 1\text{ }\Omega$	$T_j = 150^\circ\text{C}$	72		ns
t_f	$di/dt_{on} = 3400\text{ A}/\mu\text{s}$	$T_j = 150^\circ\text{C}$	15.8		mJ
E_{off}	$di/dt_{off} = 1750\text{ A}/\mu\text{s}$	$T_j = 150^\circ\text{C}$			mJ
$R_{th(j-c)}$	per IGBT			0.19	K/W



Fast IGBT4 Modules

SKM150GB12T4

Features

- IGBT4 = 4. Generation (Trench)IGBT
- VCEsat with positive temperature coefficient
- High short circuit capability, self limiting to $6 \times I_{CNOM}$
- Soft switching 4. Generation CAL diode (CAL4)

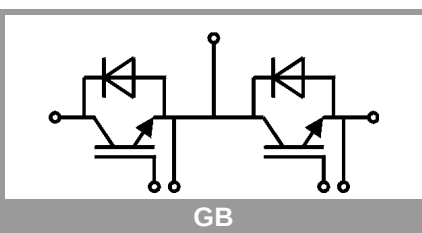
Typical Applications

- AC inverter drives
- UPS
- Electronic welders at fsw up to 20 kHz

Remarks

- Case temperature limited to $T_c = 125^\circ\text{C}$ max, recomm.
Top = $-40 \dots +150^\circ\text{C}$, product rel. results valid for $T_j = 150^\circ$

Characteristics						
Symbol	Conditions		min.	typ.	max.	Unit
Inverse diode						
$V_F = V_{EC}$	$I_F = 150\text{ A}$	$T_j = 25\text{ }^{\circ}\text{C}$		2.14	2.46	V
	$V_{GE} = 0\text{ V}$ chip	$T_j = 150\text{ }^{\circ}\text{C}$		2.07	2.38	V
V_{F0}		$T_j = 25\text{ }^{\circ}\text{C}$		1.3	1.5	V
		$T_j = 150\text{ }^{\circ}\text{C}$		0.9	1.1	V
r_F		$T_j = 25\text{ }^{\circ}\text{C}$		5.6	6.4	mΩ
		$T_j = 150\text{ }^{\circ}\text{C}$		7.8	8.5	mΩ
I_{RRM}	$I_F = 150\text{ A}$	$T_j = 150\text{ }^{\circ}\text{C}$		120		A
Q_{rr}	$di/dt_{off} = 3100\text{ A}/\mu\text{s}$	$T_j = 150\text{ }^{\circ}\text{C}$		31.3		μC
E_{rr}	$V_{GE} = \pm 15\text{ V}$ $V_{CC} = 600\text{ V}$	$T_j = 150\text{ }^{\circ}\text{C}$		13		mJ
$R_{th(j-c)}$	per diode				0.31	K/W
Module						
L_{CE}					30	nH
$R_{CC'+EE'}$	terminal-chip	$T_C = 25\text{ }^{\circ}\text{C}$		0.65		mΩ
		$T_C = 125\text{ }^{\circ}\text{C}$		1		mΩ
$R_{th(c-s)}$	per module			0.04	0.05	K/W
M_s	to heat sink M6		3		5	Nm
M_t		to terminals M5	2.5		5	Nm
						Nm
w					160	g



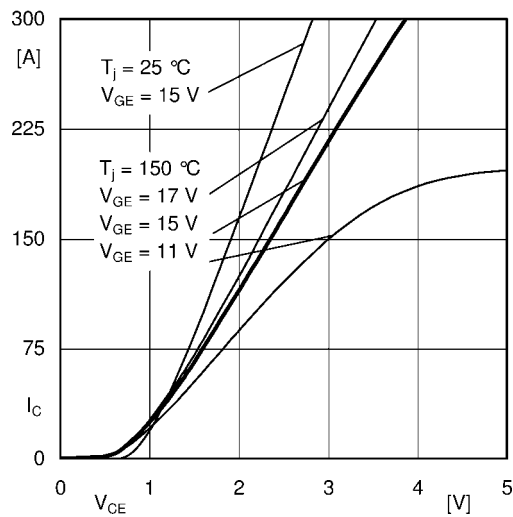


Fig. 1: Typ. output characteristic, inclusive $R_{CC'} + E_{E'}$

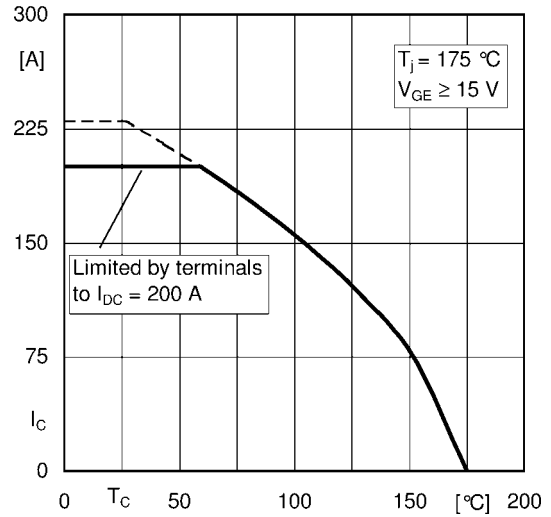


Fig. 2: Rated current vs. temperature $I_C = f(T_C)$

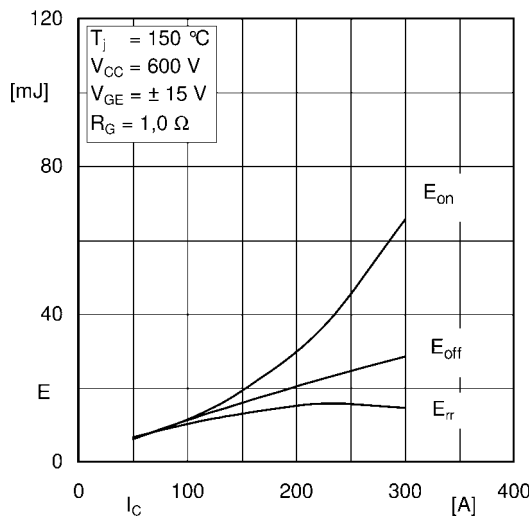


Fig. 3: Typ. turn-on /-off energy = $f(I_C)$

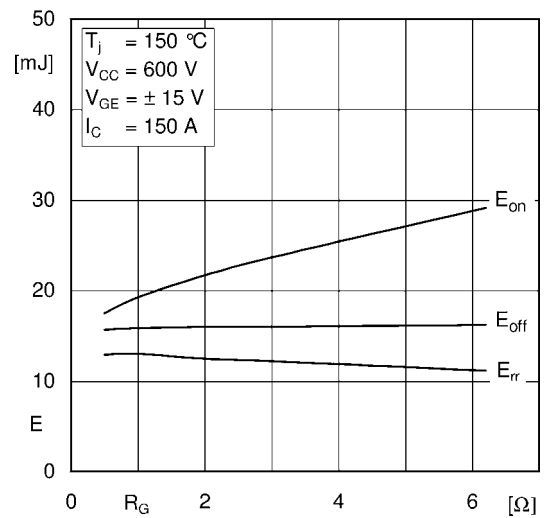


Fig. 4: Typ. turn-on /-off energy = $f(R_G)$

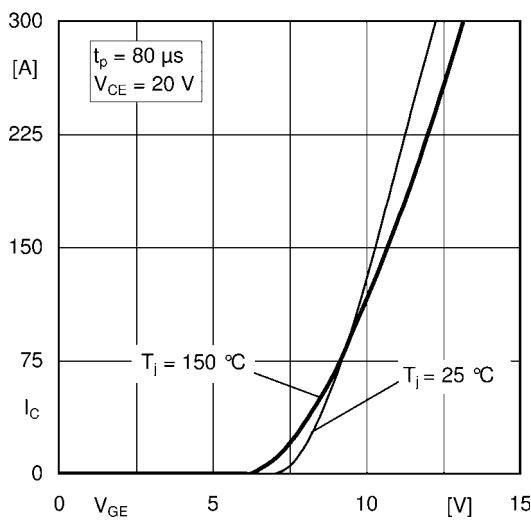


Fig. 5: Typ. transfer characteristic

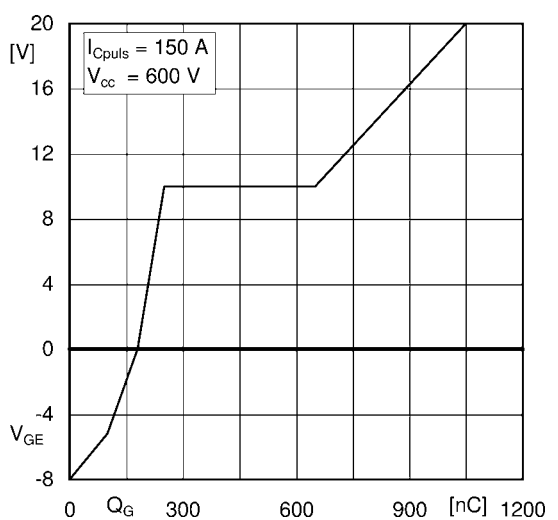


Fig. 6: Typ. gate charge characteristic

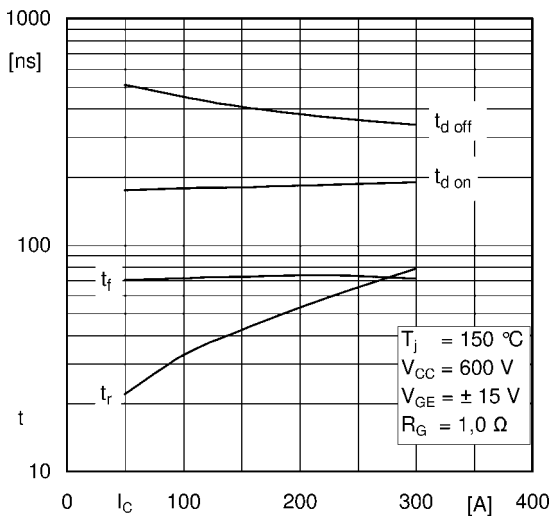


Fig. 7: Typ. switching times vs. I_C

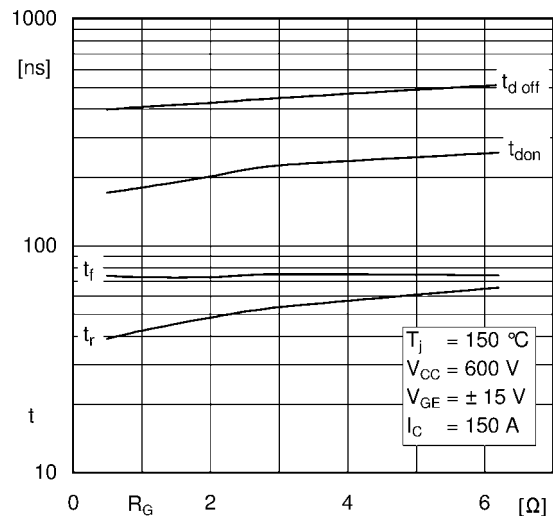


Fig. 8: Typ. switching times vs. gate resistor R_G

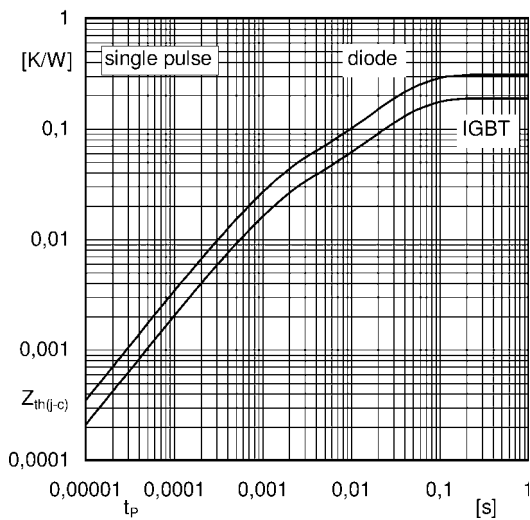


Fig. 9: Transient thermal impedance

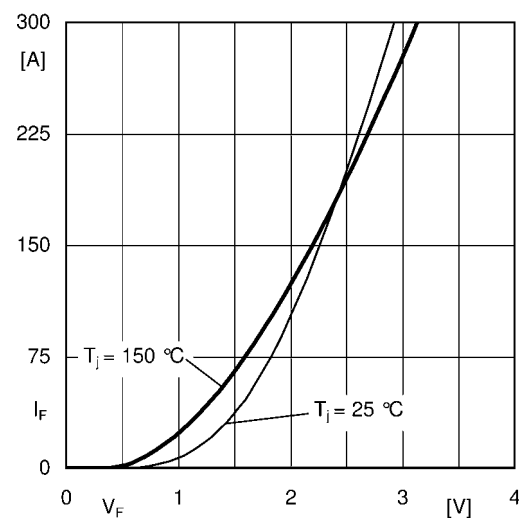


Fig. 10: CAL diode forward characteristic

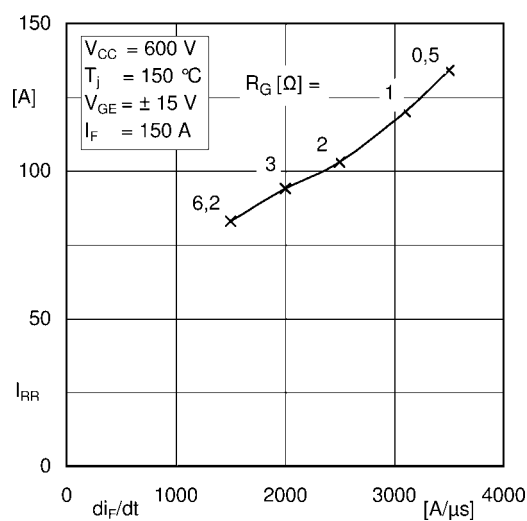


Fig. 11: CAL diode peak reverse recovery current

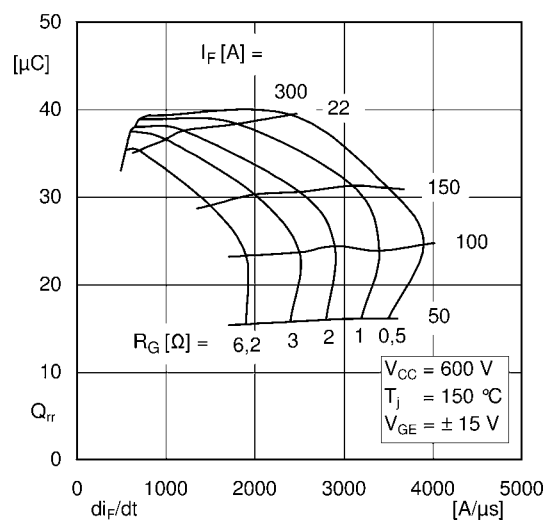
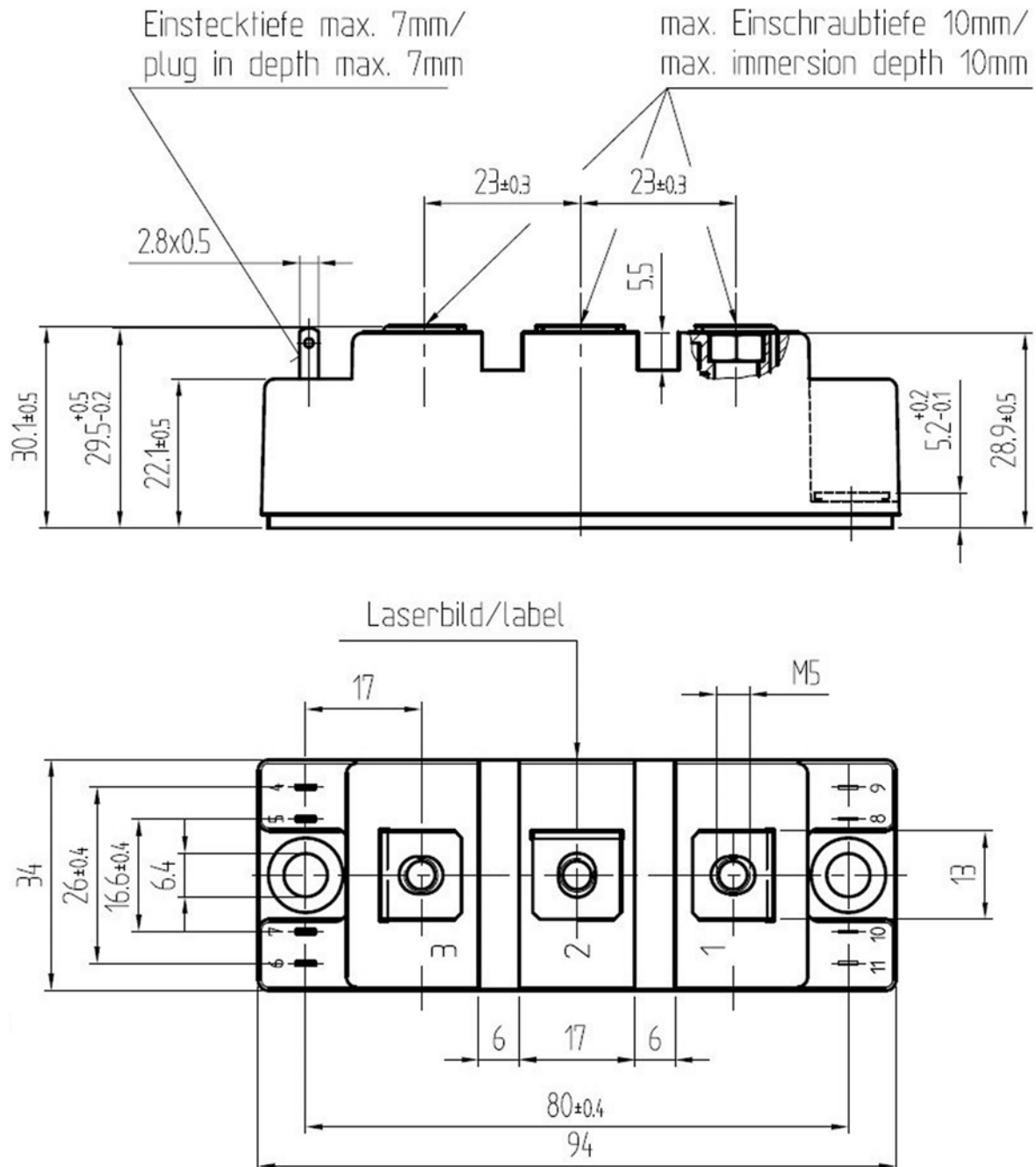
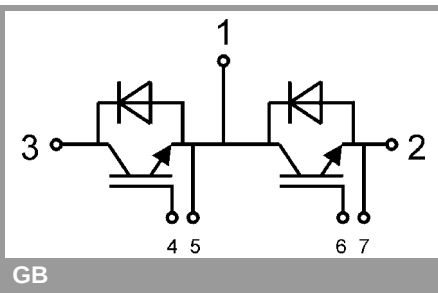


Fig. 12: Typ. CAL diode peak reverse recovery charge



Semitrans 2



This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

This technical information specifies semiconductor devices but promises no characteristics. No warranty or guarantee expressed or implied is made regarding delivery, performance or suitability.